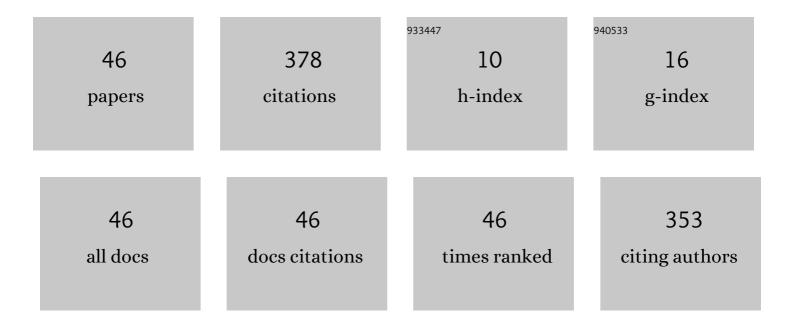
Mi?osz Grodzicki

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Properties of Thin MgO Films on 6H-SiC and GaN: Photoelectron Studies. Acta Physica Polonica A, 2022, 141, 116-122.	0.5	1
2	Interfacial Polarization of Thin Alq3, Gaq3, and Erq3 Films on GaN(0001). Materials, 2022, 15, 1671.	2.9	3
3	Detailed surface studies on the reduction of Al incorporation into AlGaN grown by molecular beam epitaxy in the Ga-droplet regime. Vacuum, 2022, 202, 111168.	3.5	4
4	Thermal oxidation of [0001] GaN in water vapor compared with dry and wet oxidation: Oxide properties and impact on GaN. Applied Surface Science, 2022, 598, 153872.	6.1	4
5	Interface formation of Al ₂ O ₃ on nâ€GaN(0001): Photoelectron spectroscopy studies. Surface and Interface Analysis, 2021, 53, 118-124.	1.8	10
6	Properties of Bare and Thin-Film-Covered GaN(0001) Surfaces. Coatings, 2021, 11, 145.	2.6	7
7	Au(100) as a Template for Pentacene Monolayer. Molecules, 2021, 26, 2393.	3.8	4
8	PHOTOELECTRON SPECTROSCOPY STUDIES ON Al2O3 FILMS ON p-GaN(0001). Surface Review and Letters, 2021, 28, 2150077.	1.1	1
9	Influence of Graphite Layer on Electronic Properties of MgO/6H-SiC(0001) Interface. Materials, 2021, 14, 4189.	2.9	5
10	Band engineering in nitrogen-rich AlGaNAs quaternary alloys. Vacuum, 2021, 189, 110240.	3.5	2
11	Growth and properties of the GaN cap layer strongly influenced by the composition of the underlying AlGaN. Materials Science in Semiconductor Processing, 2021, 136, 106125.	4.0	3
12	Temperature sensitivity modulation through changing the vanadium concentration in a La2MgTiO6:V5+,Cr3+ double perovskite optical thermometer. Dalton Transactions, 2021, 50, 9851-9857.	3.3	23
13	Influence of pulsed Al deposition on quality of Al-rich Al(Ga)N structures grown by molecular beam epitaxy. Surfaces and Interfaces, 2021, 27, 101560.	3.0	2
14	Bistable Fermi level pinning and surface photovoltage in GaN. Applied Surface Science, 2020, 533, 147416.	6.1	13
15	Interface formation of Al2O3 on carbon enriched 6H-SiC(0001): Photoelectron spectroscopy studies. Vacuum, 2020, 177, 109345.	3.5	12
16	Impact of surface photovoltage on photoemission from Ni/p-GaN. Applied Surface Science, 2020, 512, 145643.	6.1	4
17	Surface studies of physicochemical properties of As films on GaN(0001). Applied Surface Science, 2019, 493, 384-388.	6.1	11
18	Electronic properties of p-GaN co-doped with Mn by thermal process: Surface studies. Surface Science, 2019, 689, 121460.	1.9	8

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#	Article	IF	CITATIONS
19	As-related stability of the band gap temperature dependence in N-rich GaNAs. Applied Physics Letters, 2019, 115, 092106.	3.3	8
20	XPS studies on the role of arsenic incorporated into GaN. Vacuum, 2019, 167, 73-76.	3.5	24
21	MnGa and (Mn,Ga)N-like alloy formation during annealing of Mn/GaN(0001) interface. Applied Surface Science, 2019, 481, 790-794.	6.1	9
22	The Influence of Oxygen and Carbon Contaminants on the Valence Band of p-GaN(0001). Acta Physica Polonica A, 2019, 136, 585-588.	0.5	5
23	Changes of electronic properties of p-GaN(0 0 0 1) surface after low-energy N+-ion bombardment. Applied Surface Science, 2018, 440, 547-552.	6.1	20
24	Influence of ionic interfacial layers on electronic properties of Alq ₃ /Si(100) interface. Surface and Interface Analysis, 2018, 50, 623-627.	1.8	2
25	Studies of early stages of Mn/GaN(0001) interface formation using surface-sensitive techniques. Vacuum, 2018, 153, 12-16.	3.5	17
26	Electronic system for the complex measurement of a Wilberforce pendulum. European Journal of Physics, 2018, 39, 035804.	0.6	2
27	Physicochemical properties of the Sb/p-SiC interface. Vacuum, 2017, 146, 216-220.	3.5	3
28	Modification of Electronic Structure of n-GaN(0001) Surface by N ⁺ -lon Bombardment. Acta Physica Polonica A, 2017, 132, 351-353.	0.5	14
29	Ru/GaN(0001) Interface Properties. Acta Physica Polonica A, 2017, 132, 354-357.	0.5	10
30	Electronic Properties of Structures Containing Films of Alq3 and LiBr Deposited on Si(111) Crystal. Acta Physica Polonica A, 2017, 132, 357-360.	0.5	4
31	AFM studies of pits formation on KBr(1 0 0) during its dissolution by water. Materials Science-Poland, 2016, 34, 863-867.	1.0	3
32	TiO thin films on GaN(0001). Physica Status Solidi (B): Basic Research, 2015, 252, 1001-1005.	1.5	9
33	Formation of GaPd2 and GaPd intermetallic compounds on GaN(0001). Applied Physics A: Materials Science and Processing, 2015, 120, 1443-1451.	2.3	18
34	AFM/STM Modification of Thin Sb Films on 6H-SiC(0001). Acta Physica Polonica A, 2014, 126, 1131-1133.	0.5	2
35	Sb Layers on p-GaN: UPS, XPS and LEED Study. Acta Physica Polonica A, 2014, 126, 1128-1130.	0.5	8
36	Pd/GaN(0001) interface properties. Materials Science-Poland, 2014, 32, 252-256.	1.0	9

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#	Article	IF	CITATIONS
37	Effect of annealing on Ni/GaN(0001) contact morphology. Applied Surface Science, 2014, 304, 24-28.	6.1	20
38	Oxidation of GaN(0001) by low-energy ion bombardment. Applied Surface Science, 2014, 304, 20-23.	6.1	35
39	Characterization of Cr/6H-SiC(0001) nano-contacts by current-sensing AFM. Applied Surface Science, 2009, 256, 1014-1018.	6.1	5
40	Thermal stability of LiF thin films on 6H-SiC(0001) surface. Vacuum, 2009, 84, 622-624.	3.5	4
41	Formation of Excess Silicon on 6H-SiC(0001) during Hydrogen Etching. Acta Physica Polonica A, 2009, 116, S-82-S-85.	0.5	8
42	Empty core screw dislocations formed on 6H–SiC(0001) during hydrogen etching. Thin Solid Films, 2008, 516, 7530-7537.	1.8	9
43	Current patterning of 6H–SiC(0001) surface by AFM. Applied Surface Science, 2008, 254, 4332-4335.	6.1	4
44	Morphology and electric conductance of ultra-thin Cr contacts on 6H-SiC(0001): AFM and current-sensing AFM study. Vacuum, 2007, 82, 364-371.	3.5	3
45	Properties of Thin Film-Covered GaN(0001) Surfaces. , 0, , .		3
46	Topography of thin films containing Ni-Ga intermetallic compounds formed on GaN(0001). Copernican Letters, 0, 7, 1.	0.0	3